

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error Count
1	IS&R	L1	3	((("6458699") or ("6509239") or ("6159852")).PN.	USPAT; US-PGPUB	2004/04/30 11:04			0

924,426
10/050,426

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
2	BRS	L2	45	selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit \$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "SiH.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 13:56			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
				crystal\$7 with ((BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "TaO.sub.2" or TaO or "TaO"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 13:57			0
3	BRS	L3	1494						
4	BRS	L4	0	2 same 3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 11:40			0
5	BRS	L5	2	2 and 3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 11:40			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error
6	BRS	L6	35621	crystal\$7 near\$5 (dielectric or insulat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 11:43			0
7	BRS	L7	0	2 same 6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 11:43			0
8	BRS	L8	5	2 and 6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 11:43			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error
9	BRS	L9	1745	(polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit \$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "SiH.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 15:38			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
10	BRS	L10	0	3 same 9	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 11:46			0
11	BRS	L11	14	3 and 9	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 11:47			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
12	BRS	L12	428	selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit \$5) same (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 15:35			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error
13	BRS	L13	1494	(crystal\$7 or mono-crystal\$7 or (mono adj crystal\$7)) with ((BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "TaO.sub.2" or TaO or "TaO"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:01			0
14	BRS	L14	0	12 same 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 13:58			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error
15	BRS	L15	7	12 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 13:59			0
16	BRS	L16	136162	(crystal\$7 or mono-crystal\$7 or (mono adj crystal\$7)) with (dielectric or insulat\$4 or oxide or dioxide or nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:02			0
17	BRS	L17	21	12 same 16	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:02			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
18	BRS	L18	16	selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit \$5) same (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2") same ((upper or top or second) near\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:25			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error
19	BRS	L19	545331	(upper or top or second) near2 (plate\$1 or electrode\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:25			0
20	BRS	L20	16	2 and 19	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:30			0
21	BRS	L21	0	20 NOT 2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:30			0
22	BRS	L22	29	2 not 20	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:31			0
23	BRS	L23	16	12 same 19	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:58			0
24	BRS	L24	158	12 and 19	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 15:03			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error
25	BRS	L25	10117	selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (form\$4 or deposit\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 15:36			0
26	BRS	L26	223	25 and 12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 15:37			0
27	BRS	L27	44	9 with 25	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 15:40			0
28	BRS	L28	71	9 same 25	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 15:40			0
29	BRS	L29	27	28 NOT 27	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 15:41			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error
30	IS&R	L30	11	((("4497683") or ("4963506") or ("5080933") or ("5110757") or ("5124276") or ("5364815") or ("5441012") or ("5006911") or ("5818100") or ("5037775") or ("5646073")).PN.	USPAT; US-PGPUB	2004/04/30 16:25			0
31	IS&R	L31	10	((("6013575") or ("4948755") or ("4966868") or ("5607878") or ("5663098") or ("6017823") or ("6069036") or ("5798278") or ("5037778") or ("5118639")).PN.	USPAT; US-PGPUB	2004/04/30 16:27			0
32	BRS	L32	21	30 or 31	USPAT; US-PGPUB	2004/04/30 16:27			0

L Number	Hits	Search Text	DB	Time stamp
1	3	((("6458699") or ("6509239") or ("6159852"))).PN.	USPAT; US-PGPUB	2004/04/30 11:04
2	45	selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 13:56
3	1494	crystal\$7 with ((BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 13:57
4	0	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")) same (crystal\$7 with ((BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO")))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 11:40
5	2	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")) and (crystal\$7 with ((BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO")))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 11:40
6	35621	crystal\$7 near5 (dielectric or insulat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 11:43
7	0	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")) same (crystal\$7 near5 (dielectric or insulat\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 11:43
8	5	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")) and (crystal\$7 near5 (dielectric or insulat\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 11:43

9	1745	(polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 15:38
10	0	(crystal\$7 with ((BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO")))) same ((polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 11:46
11	14	(crystal\$7 with ((BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO")))) and ((polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 11:47
12	428	selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) same (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 15:35
13	1494	(crystal\$7 or mono-crystal\$7 or (mono adj crystal\$7)) with ((BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:01
14	0	(selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) same (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")) same ((crystal\$7 or mono-crystal\$7 or (mono adj crystal\$7)) with ((BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO"))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 13:58

15	7	(selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) same (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")) and ((crystal\$7 or mono-crystal\$7 or (mono adj crystal\$7)) with ((BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO"))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 13:59
16	136162	(crystal\$7 or mono-crystal\$7 or (mono adj crystal\$7)) with (dielectric or insulat\$4 or oxide or dioxide or nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:02
17	21	(selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) same (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")) same ((crystal\$7 or mono-crystal\$7 or (mono adj crystal\$7)) with (dielectric or insulat\$4 or oxide or dioxide or nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:02
18	16	selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) same (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2") same ((upper or top or second) near2 (plate\$1 or electrode\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:25
19	545331	(upper or top or second) near2 (plate\$1 or electrode\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:25
20	16	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")) and ((upper or top or second) near2 (plate\$1 or electrode\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:30

21	0	((selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")) and ((upper or top or second) near2 (plate\$1 or electrode\$1))) NOT (selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:30
22	29	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")) not ((selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")) and ((upper or top or second) near2 (plate\$1 or electrode\$1)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:31
23	16	(selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) same (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")) same ((upper or top or second) near2 (plate\$1 or electrode\$1)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:58
24	158	(selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) same (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")) and ((upper or top or second) near2 (plate\$1 or electrode\$1)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 15:03
25	10117	selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (form\$4 or deposit\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 15:36

26	223	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (form\$4 or deposit\$5)) and (selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) same (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 15:37
27	44	((polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")) with (selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (form\$4 or deposit\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 15:40
28	71	((polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")) same (selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (form\$4 or deposit\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 15:40
29	27	((polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")) same (selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (form\$4 or deposit\$5)) NOT (((polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")) with (selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (form\$4 or deposit\$5)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 15:41
30	11	((("4497683") or ("4963506") or ("5080933") or ("5110757") or ("5124276") or ("5364815") or ("5441012") or ("5006911") or ("5818100") or ("5037775") or ("5646073")).PN.	USPAT; US-PGPUB	2004/04/30 16:25
31	10	((("6013575") or ("4948755") or ("4966868") or ("5607878") or ("5663098") or ("6017823") or ("6069036") or ("5798278") or ("5037778") or ("5118639")).PN.	USPAT; US-PGPUB	2004/04/30 16:27
32	21	((("4497683") or ("4963506") or ("5080933") or ("5110757") or ("5124276") or ("5364815") or ("5441012") or ("5006911") or ("5818100") or ("5037775") or ("5646073")).PN.) or (((("6013575") or ("4948755") or ("4966868") or ("5607878") or ("5663098") or ("6017823") or ("6069036") or ("5798278") or ("5037778") or ("5118639")).PN.)	USPAT; US-PGPUB	2004/04/30 16:27
-	3	((("6458699") or ("6509239") or ("6159852")).PN.	USPAT; US-PGPUB	2003/07/13 12:00

-	431	selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5)) with (silicon or silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 11:38
-	465444	(upper or second or top or another) adj3 (plate\$1 or electrode\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/13 11:40
-	11	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5)) with (silicon or silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")) with ((upper or second or top or another) adj3 (plate\$1 or electrode\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/13 11:40
-	3	((("4497683") or ("5006911") or ("4963506")).PN.	USPAT; US-PGPUB	2003/07/13 12:02
-	25	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5)) with (silicon or silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")) same ((upper or second or top or another) adj3 (plate\$1 or electrode\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/13 12:11
-	581471	capacitor or capacitors or DRAM or DRAMs	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/13 12:12
-	5953	BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titanate) or bariumstrontiumtitanate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/13 12:14
-	26351	(tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/13 12:19
-	1480	(capacitor or capacitors or DRAM or DRAMs) and (BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titanate) or bariumstrontiumtitanate) and ((tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/13 12:43
-	1289	crystal\$7 with ((BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 11:39

-	615	((capacitor or capacitors or DRAM or DRAMs) and (crystal\$7 with ((BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO"))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/13 12:44
-	788	selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/13 12:45
-	9	((capacitor or capacitors or DRAM or DRAMs) and (crystal\$7 with ((BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO")))) and (selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5)) with (silicon or silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/13 12:47